Intel - EPF10K10ATC144-3N Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	72
Number of Logic Elements/Cells	576
Total RAM Bits	6144
Number of I/O	102
Number of Gates	31000
Voltage - Supply	3V ~ 3.6V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k10atc144-3n

The FLEX 10K architecture is similar to that of embedded gate arrays, the fastest-growing segment of the gate array market. As with standard gate arrays, embedded gate arrays implement general logic in a conventional "sea-of-gates" architecture. In addition, embedded gate arrays have dedicated die areas for implementing large, specialized functions. By embedding functions in silicon, embedded gate arrays provide reduced die area and increased speed compared to standard gate arrays. However, embedded megafunctions typically cannot be customized, limiting the designer's options. In contrast, FLEX 10K devices are programmable, providing the designer with full control over embedded megafunctions and general logic while facilitating iterative design changes during debugging.

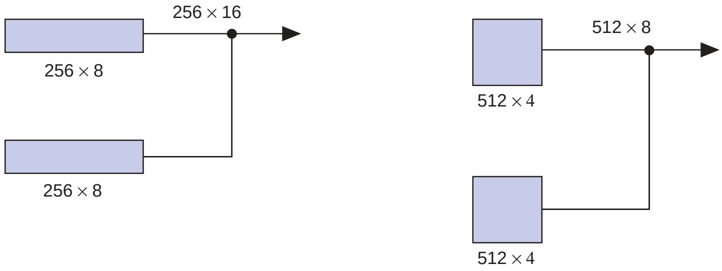
Each FLEX 10K device contains an embedded array and a logic array. The embedded array is used to implement a variety of memory functions or complex logic functions, such as digital signal processing (DSP), microcontroller, wide-data-path manipulation, and data-transformation functions. The logic array performs the same function as the sea-of-gates in the gate array: it is used to implement general logic, such as counters, adders, state machines, and multiplexers. The combination of embedded and logic arrays provides the high performance and high density of embedded gate arrays, enabling designers to implement an entire system on a single device.

FLEX 10K devices are configured at system power-up with data stored in an Altera serial configuration device or provided by a system controller. Altera offers the EPC1, EPC2, EPC16, and EPC1441 configuration devices, which configure FLEX 10K devices via a serial data stream. Configuration data can also be downloaded from system RAM or from Altera's BitBlaster™ serial download cable or ByteBlasterMV™ parallel port download cable. After a FLEX 10K device has been configured, it can be reconfigured in-circuit by resetting the device and loading new data. Because reconfiguration requires less than 320 ms, real-time changes can be made during system operation.

FLEX 10K devices contain an optimized interface that permits microprocessors to configure FLEX 10K devices serially or in parallel, and synchronously or asynchronously. The interface also enables microprocessors to treat a FLEX 10K device as memory and configure the device by writing to a virtual memory location, making it very easy for the designer to reconfigure the device.

Larger blocks of RAM are created by combining multiple EABs. For example, two 256 × 8 RAM blocks can be combined to form a 256 × 16 RAM block; two 512 × 4 blocks of RAM can be combined to form a 512 × 8 RAM block. See Figure 3.

Figure 3. Examples of Combining EABs



If necessary, all EABs in a device can be cascaded to form a single RAM block. EABs can be cascaded to form RAM blocks of up to 2,048 words without impacting timing. Altera's software automatically combines EABs to meet a designer's RAM specifications.

EABs provide flexible options for driving and controlling clock signals. Different clocks can be used for the EAB inputs and outputs. Registers can be independently inserted on the data input, EAB output, or the address and `WE` inputs. The global signals and the EAB local interconnect can drive the `WE` signal. The global signals, dedicated clock pins, and EAB local interconnect can drive the EAB clock signals. Because the LEs drive the EAB local interconnect, the LEs can control the `WE` signal or the EAB clock signals.

Each EAB is fed by a row interconnect and can drive out to row and column interconnects. Each EAB output can drive up to two row channels and up to two column channels; the unused row channel can be driven by other LEs. This feature increases the routing resources available for EAB outputs. See Figure 4.

During compilation, the Compiler automatically selects the best control signal implementation. Because the clear and preset functions are active-low, the Compiler automatically assigns a logic high to an unused clear or preset.

The clear and preset logic is implemented in one of the following six modes chosen during design entry:

- Asynchronous clear
- Asynchronous preset
- Asynchronous clear and preset
- Asynchronous load with clear
- Asynchronous load with preset
- Asynchronous load without clear or preset

In addition to the six clear and preset modes, FLEX 10K devices provide a chip-wide reset pin that can reset all registers in the device. Use of this feature is set during design entry. In any of the clear and preset modes, the chip-wide reset overrides all other signals. Registers with asynchronous presets may be preset when the chip-wide reset is asserted. Inversion can be used to implement the asynchronous preset. Figure 10 shows examples of how to enter a section of a design for the desired functionality.

Table 8. EPF10K10, EPF10K20, EPF10K30, EPF10K40 & EPF10K50 Peripheral Bus Sources

Peripheral Control Signal	EPF10K10 EPF10K10A	EPF10K20	EPF10K30 EPF10K30A	EPF10K40	EPF10K50 EPF10K50V
OE0	Row A	Row A	Row A	Row A	Row A
OE1	Row A	Row B	Row B	Row C	Row B
OE2	Row B	Row C	Row C	Row D	Row D
OE3	Row B	Row D	Row D	Row E	Row F
OE4	Row C	Row E	Row E	Row F	Row H
OE5	Row C	Row F	Row F	Row G	Row J
CLKENA0/CLK0/GLOBAL0	Row A	Row A	Row A	Row B	Row A
CLKENA1/OE6/GLOBAL1	Row A	Row B	Row B	Row C	Row C
CLKENA2/CLR0	Row B	Row C	Row C	Row D	Row E
CLKENA3/OE7/GLOBAL2	Row B	Row D	Row D	Row E	Row G
CLKENA4/CLR1	Row C	Row E	Row E	Row F	Row I
CLKENA5/CLK1/GLOBAL3	Row C	Row F	Row F	Row H	Row J

Table 9. EPF10K70, EPF10K100, EPF10K130V & EPF10K250A Peripheral Bus Sources

Peripheral Control Signal	EPF10K70	EPF10K100 EPF10K100A	EPF10K130V	EPF10K250A
OE0	Row A	Row A	Row C	Row E
OE1	Row B	Row C	Row E	Row G
OE2	Row D	Row E	Row G	Row I
OE3	Row I	Row L	Row N	Row P
OE4	Row G	Row I	Row K	Row M
OE5	Row H	Row K	Row M	Row O
CLKENA0/CLK0/GLOBAL0	Row E	Row F	Row H	Row J
CLKENA1/OE6/GLOBAL1	Row C	Row D	Row F	Row H
CLKENA2/CLR0	Row B	Row B	Row D	Row F
CLKENA3/OE7/GLOBAL2	Row F	Row H	Row J	Row L
CLKENA4/CLR1	Row H	Row J	Row L	Row N
CLKENA5/CLK1/GLOBAL3	Row E	Row G	Row I	Row K

Table 12 describes the FLEX 10K device supply voltages and MultiVolt I/O support levels.

Table 12. Supply Voltages & MultiVolt I/O Support Levels

Devices	Supply Voltage (V)		MultiVolt I/O Support Levels (V)	
	V_{CCINT}	V_{CCIO}	Input	Output
FLEX 10K *(1)*	5.0	5.0	3.3 or 5.0	5.0
	5.0	3.3	3.3 or 5.0	3.3 or 5.0
EPF10K50V *(1)*	3.3	3.3	3.3 or 5.0	3.3 or 5.0
EPF10K130V	3.3	3.3	3.3 or 5.0	3.3 or 5.0
FLEX 10KA *(1)*	3.3	3.3	2.5, 3.3, or 5.0	3.3 or 5.0
	3.3	2.5	2.5, 3.3, or 5.0	2.5

Note

(1) 240-pin QFP packages do not support the MultiVolt I/O features, so they do not have separate V_{CCIO} pins.

Power Sequencing & Hot-Socketing

Because FLEX 10K devices can be used in a multi-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. The V_{CCIO} and V_{CCINT} power supplies can be powered in any order.

Signals can be driven into FLEX 10KA devices before and during power up without damaging the device. Additionally, FLEX 10KA devices do not drive out during power up. Once operating conditions are reached, FLEX 10KA devices operate as specified by the user.

IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All FLEX 10K devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1-1990 specification. All FLEX 10K devices can also be configured using the JTAG pins through the BitBlaster serial download cable, or ByteBlasterMV parallel port download cable, or via hardware that uses the Jam™ programming and test language. JTAG BST can be performed before or after configuration, but not during configuration. FLEX 10K devices support the JTAG instructions shown in Table 13.

Table 19. FLEX 10K 5.0-V Device DC Operating Conditions *Notes (5), (6)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		2.0		V_{CCINT} + 0.5	V
V_{IL}	Low-level input voltage		–0.5		0.8	V
V_{OH}	5.0-V high-level TTL output voltage	I_{OH} = –4 mA DC, V_{CCIO} = 4.75 V *(7)*	2.4			V
	3.3-V high-level TTL output voltage	I_{OH} = –4 mA DC, V_{CCIO} = 3.00 V *(7)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(7)*	V_{CCIO} – 0.2			V
V_{OL}	5.0-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 4.75 V *(8)*			0.45	V
	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(8)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(8)*			0.2	V
I_I	Input pin leakage current	V_I = V_{CC} or ground *(9)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = V_{CC} or ground *(9)*	–40		40	µA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load		0.5	10	mA

Table 20. 5.0-V Device Capacitance of EPF10K10, EPF10K20 & EPF10K30 Devices *Note (10)*

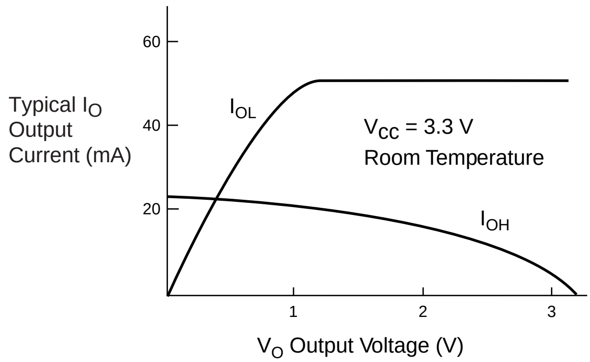
Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Table 21. 5.0-V Device Capacitance of EPF10K40, EPF10K50, EPF10K70 & EPF10K100 Devices *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		15	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		10	pF

Figure 21 shows the typical output drive characteristics of EPF10K50V and EPF10K130V devices.

Figure 21. Output Drive Characteristics of EPF10K50V & EPF10K130V Devices



Tables 26 through 31 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 3.3-V FLEX 10K devices.

Table 26. FLEX 10KA 3.3-V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	Supply voltage	With respect to ground *(2)*	–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	Ceramic packages, under bias		150	° C
		PQFP, TQFP, RQFP, and BGA packages, under bias		135	° C

Notes to tables:

(1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.

(2) Operating conditions: V_{CCIO} = 5.0 V ± 5% for commercial use in FLEX 10K devices.
V_{CCIO} = 5.0 V ± 10% for industrial use in FLEX 10K devices.
V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10KA devices.

(3) Operating conditions: V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10K devices.
V_{CCIO} = 2.5 V ± 0.2 V for commercial or industrial use in FLEX 10KA devices.

(4) Operating conditions: V_{CCIO} = 2.5 V, 3.3 V, or 5.0 V.

(5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the `WE` signal is registered.

(6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.

(7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.

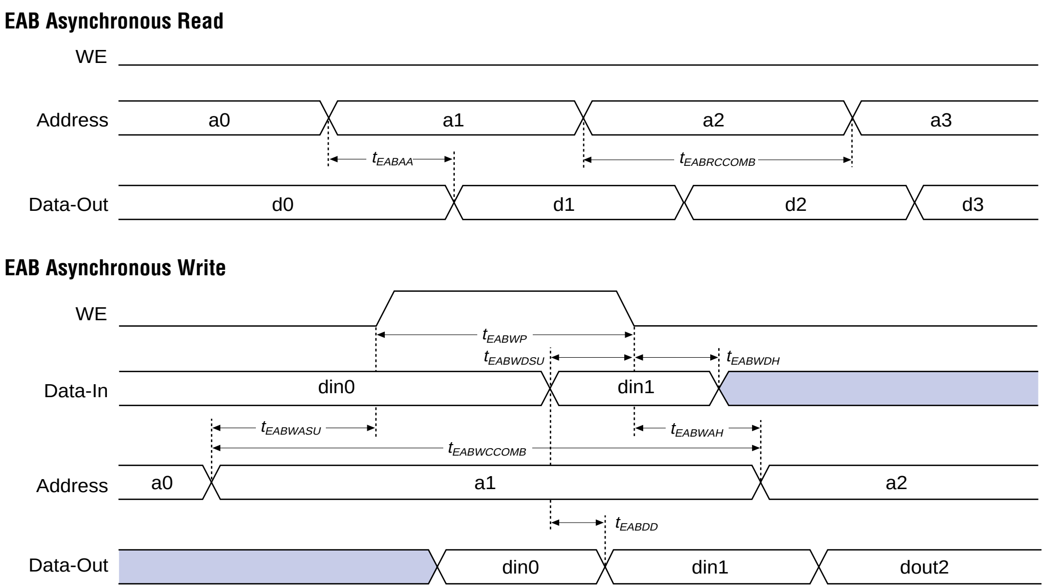
(8) External reference timing parameters are factory-tested, worst-case values specified by Altera. A representative subset of signal paths is tested to approximate typical device applications.

(9) Contact Altera Applications for test circuit specifications and test conditions.

(10) These timing parameters are sample-tested only.

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, for the EAB macroparameters in Table 34.

Figure 29. EAB Asynchronous Timing Waveforms



Tables 39 through 47 show EPF10K10 and EPF10K20 device internal and external timing parameters.

Table 39. EPF10K10 & EPF10K20 Device LE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{LUT}		1.4		1.7	ns
t_{CLUT}		0.6		0.7	ns
t_{RLUT}		1.5		1.9	ns
t_{PACKED}		0.6		0.9	ns
t_{EN}		1.0		1.2	ns
t_{CICO}		0.2		0.3	ns
t_{CGEN}		0.9		1.2	ns
t_{CGENR}		0.9		1.2	ns
t_{CASC}		0.8		0.9	ns
t_{C}		1.3		1.5	ns
t_{CO}		0.9		1.1	ns
t_{COMB}		0.5		0.6	ns
t_{SU}	1.3		2.5		ns
t_{H}	1.4		1.6		ns
t_{PRE}		1.0		1.2	ns
t_{CLR}		1.0		1.2	ns
t_{CH}	4.0		4.0		ns
t_{CL}	4.0		4.0		ns

Table 40. EPF10K10 & EPF10K20 Device IOE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{IOD}		1.3		1.6	ns
t_{IOC}		0.5		0.7	ns
t_{IOCO}		0.2		0.2	ns
t_{IOCOMB}		0.0		0.0	ns
t_{IOSU}	2.8		3.2		ns
t_{IOH}	1.0		1.2		ns
t_{IOCLR}		1.0		1.2	ns
t_{OD1}		2.6		3.5	ns
t_{OD2}		4.9		6.4	ns
t_{OD3}		6.3		8.2	ns
t_{XZ}		4.5		5.4	ns
t_{ZX1}		4.5		5.4	ns
t_{ZX2}		6.8		8.3	ns
t_{ZX3}		8.2		10.1	ns
t_{INREG}		6.0		7.5	ns
t_{IOFD}		3.1		3.5	ns
t_{INCOMB}		3.1		3.5	ns

Table 43. EPF10K10 Device Interconnect Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.8		6.2	ns
t_{DIN2LE}		2.6		3.8	ns
$t_{DIN2DATA}$		4.3		5.2	ns
$t_{DCLK2IOE}$		3.4		4.0	ns
$t_{DCLK2LE}$		2.6		3.8	ns
$t_{SAMELAB}$		0.6		0.6	ns
$t_{SAMEROW}$		3.6		3.8	ns
$t_{SAMECOLUMN}$		0.9		1.1	ns
$t_{DIFFROW}$		4.5		4.9	ns
$t_{TWOROWS}$		8.1		8.7	ns
$t_{LEPERIPH}$		3.3		3.9	ns
$t_{LABCARRY}$		0.5		0.8	ns
$t_{LABCASC}$		2.7		3.0	ns

Table 44. EPF10K20 Device Interconnect Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{DIN2IOE}$		5.2		6.6	ns
t_{DIN2LE}		2.6		3.8	ns
$t_{DIN2DATA}$		4.3		5.2	ns
$t_{DCLK2IOE}$		4.3		4.0	ns
$t_{DCLK2LE}$		2.6		3.8	ns
$t_{SAMELAB}$		0.6		0.6	ns
$t_{SAMEROW}$		3.7		3.9	ns
$t_{SAMECOLUMN}$		1.4		1.6	ns
$t_{DIFFROW}$		5.1		5.5	ns
$t_{TWOROWS}$		8.8		9.4	ns
$t_{LEPERIPH}$		4.7		5.6	ns
$t_{LABCARRY}$		0.5		0.8	ns
$t_{LABCASC}$		2.7		3.0	ns

Table 59. EPF10K70 Device EAB Internal Microparameters *Note (1)*							
Symbol	**-2 Speed Grade**		**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
$t_{EABDATA1}$		1.3		1.5		1.9	ns
$t_{EABDATA2}$		4.3		4.8		6.0	ns
t_{EABWE1}		0.9		1.0		1.2	ns
t_{EABWE2}		4.5		5.0		6.2	ns
t_{EABCLK}		0.9		1.0		2.2	ns
t_{EABCO}		0.4		0.5		0.6	ns
$t_{EABBYPASS}$		1.3		1.5		1.9	ns
t_{EABSU}	1.3		1.5		1.8		ns
t_{EABH}	1.8		2.0		2.5		ns
t_{AA}		7.8		8.7		10.7	ns
t_{WP}	5.2		5.8		7.2		ns
t_{WDSU}	1.4		1.6		2.0		ns
t_{WDH}	0.3		0.3		0.4		ns
t_{WASU}	0.4		0.5		0.6		ns
t_{WAH}	0.9		1.0		1.2		ns
t_{WO}		4.5		5.0		6.2	ns
t_{DD}		4.5		5.0		6.2	ns
t_{EABOUT}		0.4		0.5		0.6	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	5.2		5.8		7.2		ns

Notes to tables:

(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 64 through 70 show EPF10K100 device internal and external timing parameters.

Table 64. EPF10K100 Device LE Timing Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.5		1.5		2.0	ns
t_{CLUT}		0.4		0.4		0.5	ns
t_{RLUT}		1.6		1.6		2.0	ns
t_{PACKED}		0.9		0.9		1.3	ns
t_{EN}		0.9		0.9		1.2	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		1.1		1.1		1.4	ns
t_{CGENR}		1.2		1.2		1.5	ns
t_{CASC}		1.1		1.1		1.3	ns
t_C		0.8		0.8		1.0	ns
t_{CO}		1.0		1.0		1.4	ns
t_{COMB}		0.5		0.5		0.7	ns
t_{SU}	2.1		2.1		2.6		ns
t_H	2.3		2.3		3.1		ns
t_{PRE}		1.0		1.0		1.4	ns
t_{CLR}		1.0		1.0		1.4	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Tables 71 through 77 show EPF10K50V device internal and external timing parameters.

Table 71. EPF10K50V Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.0		1.3		1.6	ns
t_{CLUT}		0.1		0.5		0.6		0.6	ns
t_{RLUT}		0.5		0.8		0.9		1.0	ns
t_{PACKED}		0.4		0.4		0.5		0.7	ns
t_{EN}		0.7		0.9		1.1		1.4	ns
t_{CICO}		0.2		0.2		0.2		0.3	ns
t_{CGEN}		0.8		0.7		0.8		1.2	ns
t_{CGENR}		0.4		0.3		0.3		0.4	ns
t_{CASC}		0.7		0.7		0.8		0.9	ns
t_C		0.3		1.0		1.3		1.5	ns
t_{CO}		0.5		0.7		0.9		1.0	ns
t_{COMB}		0.4		0.4		0.5		0.6	ns
t_{SU}	0.8		1.6		2.2		2.5		ns
t_H	0.5		0.8		1.0		1.4		ns
t_{PRE}		0.8		0.4		0.5		0.5	ns
t_{CLR}		0.8		0.4		0.5		0.5	ns
t_{CH}	2.0		4.0		4.0		4.0		ns
t_{CL}	2.0		4.0		4.0		4.0		ns

Table 72. EPF10K50V Device IOE Timing Microparameters *Note (1)*									
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{IOD}		1.2		1.6		1.9		2.1	ns
t_{IOC}		0.3		0.4		0.5		0.5	ns
t_{IOCO}		0.3		0.3		0.4		0.4	ns
t_{IOCOMB}		0.0		0.0		0.0		0.0	ns
t_{IOSU}	2.8		2.8		3.4		3.9		ns
t_{IOH}	0.7		0.8		1.0		1.4		ns
t_{IOCLR}		0.5		0.6		0.7		0.7	ns
t_{OD1}		2.8		3.2		3.9		4.7	ns
t_{OD2}		–		–		–		–	ns
t_{OD3}		6.5		6.9		7.6		8.4	ns
t_{XZ}		2.8		3.1		3.8		4.6	ns
t_{ZX1}		2.8		3.1		3.8		4.6	ns
t_{ZX2}		–		–		–		–	ns
t_{ZX3}		6.5		6.8		7.5		8.3	ns
t_{INREG}		5.0		5.7		7.0		9.0	ns
t_{IOFD}		1.5		1.9		2.3		2.7	ns
t_{INCOMB}		1.5		1.9		2.3		2.7	ns

Table 75. EPF10K50V Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.7		6.0		7.1		8.2	ns
t_{DIN2LE}		2.5		2.6		3.1		3.9	ns
$t_{DIN2DATA}$		4.4		5.9		6.8		7.7	ns
$t_{DCLK2IOE}$		2.5		3.9		4.7		5.5	ns
$t_{DCLK2LE}$		2.5		2.6		3.1		3.9	ns
$t_{SAMELAB}$		0.2		0.2		0.3		0.3	ns
$t_{SAMEROW}$		2.8		3.0		3.2		3.4	ns
$t_{SAMECOLUMN}$		3.0		3.2		3.4		3.6	ns
$t_{DIFFROW}$		5.8		6.2		6.6		7.0	ns
$t_{TWOROWS}$		8.6		9.2		9.8		10.4	ns
$t_{LEPERIPH}$		4.5		5.5		6.1		7.0	ns
$t_{LABCARRY}$		0.3		0.4		0.5		0.7	ns
$t_{LABCASC}$		0.0		1.3		1.6		2.0	ns

Table 76. EPF10K50V Device External Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{DRR}		11.2		14.0		17.2		21.1	ns
t_{INSU} *(2), (3)*	5.5		4.2		5.2		6.9		ns
t_{INH} *(3)*	0.0		0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.9	2.0	7.8	2.0	9.5	2.0	11.1	ns

Table 77. EPF10K50V Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.0		2.8		3.5		4.1		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	5.9	2.0	7.8	2.0	9.5	2.0	11.1	ns
$t_{XZBIDIR}$		8.0		9.8		11.8		14.3	ns
$t_{ZXBIDIR}$		8.0		9.8		11.8		14.3	ns

Table 81. EPF10K130V Device EAB Internal Timing Macroparameters *Note (1)*							
Symbol	**-2 Speed Grade**		**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{EABAA}		11.2		14.2		14.2	ns
$t_{EABRCCOMB}$	11.1		14.2		14.2		ns
$t_{EABRCREG}$	8.5		10.8		10.8		ns
t_{EABWP}	3.7		4.7		4.7		ns
$t_{EABWCCOMB}$	7.6		9.7		9.7		ns
$t_{EABWCREG}$	14.0		17.8		17.8		ns
t_{EABDD}		11.1		14.2		14.2	ns
$t_{EABDATACO}$		3.6		4.6		4.6	ns
$t_{EABDATASU}$	4.4		5.6		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	4.4		5.6		5.6		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	4.6		5.9		5.9		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.9		5.0		5.0		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		11.1		14.2		14.2	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 85 through 91 show EPF10K10A device internal and external timing parameters.

Table 85. EPF10K10A Device LE Timing Microparameters Note (1)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.2		1.6	ns
t_{CLUT}		1.2		1.4		1.9	ns
t_{RLUT}		1.9		2.3		3.0	ns
t_{PACKED}		0.6		0.7		0.9	ns
t_{EN}		0.5		0.6		0.8	ns
t_{CICO}		02		0.3		0.4	ns
t_{CGEN}		0.7		0.9		1.1	ns
t_{CGENR}		0.7		0.9		1.1	ns
t_{CASC}		1.0		1.2		1.7	ns
t_{C}		1.2		1.4		1.9	ns
t_{CO}		0.5		0.6		0.8	ns
t_{COMB}		0.5		0.6		0.8	ns
t_{SU}	1.1		1.3		1.7		ns
t_{H}	0.6		0.7		0.9		ns
t_{PRE}		0.5		0.6		0.9	ns
t_{CLR}		0.5		0.6		0.9	ns
t_{CH}	3.0		3.5		4.0		ns
t_{CL}	3.0		3.5		4.0		ns

Table 86. EPF10K10A Device IOE Timing Microparameters Note (1) **(Part 1 of 2)**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
		1.3		1.5		2.0	ns
t_{IOC}		0.2		0.3		0.3	ns
t_{IOCO}		0.2		0.3		0.4	ns
t_{IOCOMB}		0.6		0.7		0.9	ns
t_{IOSU}	0.8		1.0		1.3		ns

Table 100. EPF10K100A Device IOE Timing Microparameters *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{IOD}		2.5		2.9		3.4	ns
t_{IOC}		0.3		0.3		0.4	ns
t_{IOCO}		0.2		0.2		0.3	ns
t_{IOCOMB}		0.5		0.6		0.7	ns
t_{IOSU}	1.3		1.7		1.8		ns
t_{IOH}	0.2		0.2		0.3		ns
t_{IOCLR}		1.0		1.2		1.4	ns
t_{OD1}		2.2		2.6		3.0	ns
t_{OD2}		4.5		5.3		6.1	ns
t_{OD3}		6.8		7.9		9.3	ns
t_{XZ}		2.7		3.1		3.7	ns
t_{ZX1}		2.7		3.1		3.7	ns
t_{ZX2}		5.0		5.8		6.8	ns
t_{ZX3}		7.3		8.4		10.0	ns
t_{INREG}		5.3		6.1		7.2	ns
t_{IOFD}		4.7		5.5		6.4	ns
t_{INCOMB}		4.7		5.5		6.4	ns

Notes: